

ABSTRACT OF DISCLOSURE

Numerous embodiments of a stacked device underfill and a method of formation are disclosed. In one embodiment, a method of forming stacked semiconductor device with an underfill comprises forming one or more layers of compliant material on at least a portion of the top surface of a substrate, said substrate, curing at least a portion of the semiconductor device, selectively removing a portion of the one or more layers of compliant material, and assembling the substrate into a stacked semiconductor device.